New Jersey Semi-Conductor Products, Inc.

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PARAMETERS

2N6770
N-CHANNEL ENHANCEMENT MOSFET

Description: N-Channel Enhancement MOSFET

Manufacturer	
Mil/High-Rel? (Y/N)	
Vbr DSS	500
Id Max. (A)	12
Max. PD (W)	150
Derate (Amb) (W/*x*C)	1.2
R(ds) On (*j*)	400m*r*
gfs Min	8.0
gfs Max	24
I(d) for G(fs)	7.8
Vp Max	4.0
Ciss Max. (F)	3.0n
Idss Max. (A)	1.0m
Tr Max. (s)	50n
t(f) Max. (S)	70n
Vbr GSS	500*M*
Oper. Temp (*x*C) Max	150*u*
td(on) Max (S)	
t(stor) Max. (S)	
Pkg Style	TO-204AA
Surface Mounted (Y/N)	N
Pinout Equivalence Number	3-32

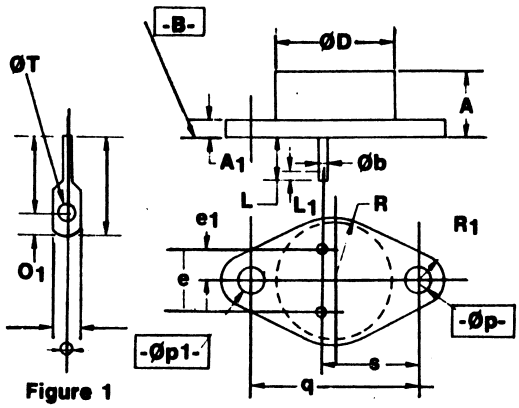


Figure 1

u Junction Temperature *r* Maximum *2* It(rms) *M* BVDGS

SYMBOL	AA MIN.	AA MAX.	NOTE
A	8.4	11.4	
A_1	–	3.42	
b	–	–	
Øb	.966	1.092	3
ØD	–	22.22	
e	10.67	11.17	
e_1	5.21	5.21	
L	7.93	–	3
L_1	–	–	
O	–	–	
O_1	–	–	
Øp	3.84	4.08	5,9
Øp	3.84	4.08	5,9
q	38.15 BSC		
R	–	13.33	
R_1	–	4.77	6
S	16.64	17.14	
ØT	–	–	
NOTE	1,2,8,9,10,11		

NOTES:

1. Refer to applicable symbol list.
2. Dimensioning and tolerancing per ansi Y14.5, 1973.
3. Two leads.
4. Square or radius on end of terminal optional.
5. Two holes.
6. Both ends.
7. Figure 1 lead configuration applicable.
8. Datum surface -B- is seating plane.
9. Dimensions -Øp- & -Øp1- are datums.
10. Positional tolerance for ØD:

⌖	Ø.25 Ⓜ	B	Øp1 Ⓜ	ØR Ⓜ

11. Controlling dimension: Millimeters

Quality Semi-Conductors